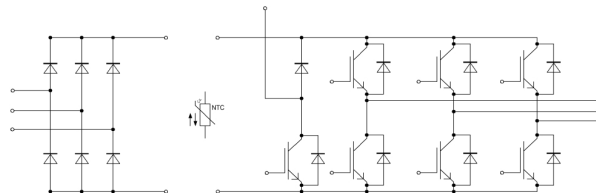
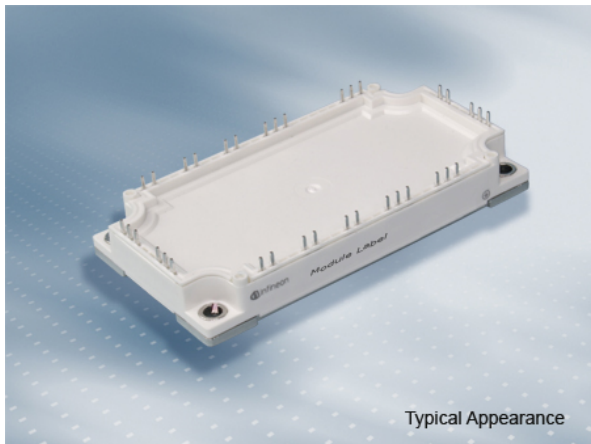


EconoPIM™3 Modul mit Trench/Feldstopp IGBT4 und Emitter Controlled Diode und NTC
EconoPIM™3 module with Trench/Fieldstop IGBT4 and Emitter Controlled diode and NTC



$V_{CES} = 1700V$
 $I_{C\ nom} = 75A / I_{CRM} = 150A$

Typische Anwendungen

- Motorantriebe

Elektrische Eigenschaften

- Erweiterte Sperrschichttemperatur $T_{vj\ op}$
- Niedriges V_{CEsat}
- Trench IGBT 4
- V_{CEsat} mit positivem Temperaturkoeffizienten

Mechanische Eigenschaften

- Integrierter NTC Temperatur Sensor
- Isolierte Bodenplatte
- Lötverbindungstechnik
- Standardgehäuse

Typical Applications

- Motor drives

Electrical Features

- Extended operating temperature $T_{vj\ op}$
- Low V_{CEsat}
- Trench IGBT 4
- V_{CEsat} with positive temperature coefficient

Mechanical Features

- Integrated NTC temperature sensor
- Isolated base plate
- Solder contact technology
- Standard housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: MB	date of publication: 2016-06-07	
approved by: RS	revision: V3.0	UL approved (E83335)



IGBT, Wechselrichter / IGBT, Inverter
Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	75 125	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	150	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	P_{tot}	555	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,95 2,35 2,45	2,30	V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 3,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,25	5,80	6,35 V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,90		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	8,5		Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	6,80		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,22		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,23 0,25 0,26		μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,036 0,04 0,045		μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,46 0,60 0,64		μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,08 0,15 0,16		μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2150\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	13,0 19,0 20,0		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	14,5 25,0 28,5		mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 1000\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	350		A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}		0,270	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,120		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0

Diode, Wechselrichter / Diode, Inverter

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
Dauergleichstrom Continuous DC forward current		I_F	75	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	150	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1350 1150	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 75\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 75\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 75\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,80 1,90 1,95	2,20	V V V
Rückstromspitze Peak reverse recovery current	$I_F = 75\text{ A}, -di_F/dt = 2150\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	105 125 130		A A A
Sperrverzögerungsladung Recovered charge	$I_F = 75\text{ A}, -di_F/dt = 2150\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	13,5 25,5 29,5		μC μC μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 75\text{ A}, -di_F/dt = 2150\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	8,60 17,0 20,0		mJ mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		R_{thJC}		0,480	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,210		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

Diode, Gleichrichter / Diode, Rectifier

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1800	V
Durchlassstrom Grenzeffektivwert pro Chip Maximum RMS forward current per chip	$T_C = 80^{\circ}\text{C}$	I_{FRMSM}	80	A
Gleichrichter Ausgang Grenzeffektivstrom Maximum RMS current at rectifier output	$T_C = 80^{\circ}\text{C}$	I_{RMSM}	140	A
Stoßstrom Grenzwert Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	600 470	A A
Grenzlastintegral I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1800 1100	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 75\text{ A}$	V_F		1,15		V
Sperrstrom Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1800\text{ V}$	I_R		1,00		mA
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode	R_{thJC}			0,650	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		0,288		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0



IGBT, Brems-Chopper / IGBT, Brake-Chopper
Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	75 150	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	150	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$	P_{tot}	555	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,95 2,35 2,45	2,30	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 3,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80	6,40	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,90			μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	8,5			Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	6,80			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,22			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,23 0,25 0,26			μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,036 0,04 0,045			μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,46 0,60 0,64			μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,08 0,15 0,16			μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2150\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	13,0 19,0 20,0			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 75\text{ A}, V_{CE} = 900\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 4,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	14,5 25,0 28,5			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 1000\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	350			A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}			0,270	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}		0,120		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0



Diode, Brems-Chopper / Diode, Brake-Chopper
Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
Dauergleichstrom Continuous DC forward current		I_F	50	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	100	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	310	A^2s
	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$		260	A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,80	2,20	V
	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	V_F	1,90		V
	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		1,95		V
Rückstromspitze Peak reverse recovery current	$I_F = 50\text{ A}, -di_F/dt = 1500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$		55,0		A
	$V_R = 900\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	I_{RM}	64,0		A
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		68,0		A
Sperrverzögerungsladung Recovered charge	$I_F = 50\text{ A}, -di_F/dt = 1500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$		15,0		μC
	$V_R = 900\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	Q_r	21,5		μC
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		24,5		μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 50\text{ A}, -di_F/dt = 1500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$		10,0		mJ
	$V_R = 900\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	E_{rec}	13,5		mJ
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		16,0		mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode	R_{thJC}			0,630	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		0,279		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}		5,00		$\text{k}\Omega$
Abweichung von R100 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
Verlustleistung Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0



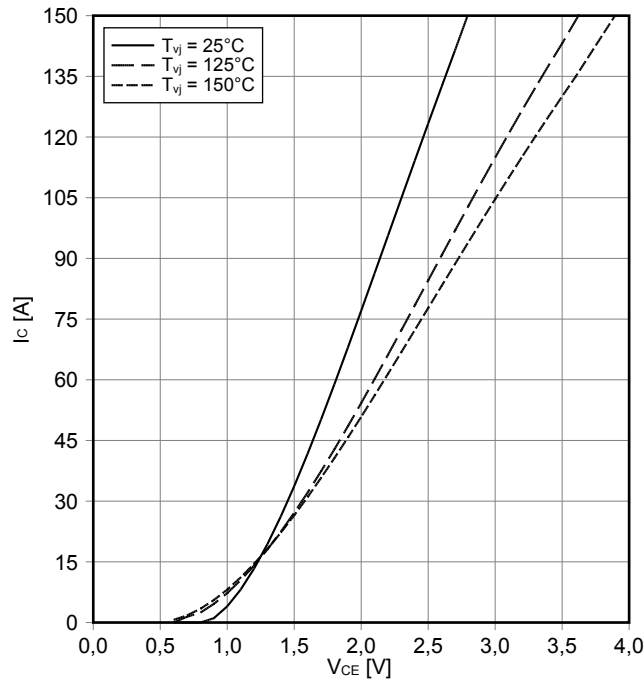
Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	3,4		kV
Material Modulgrundplatte Material of module baseplate			Cu		
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		10,0		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		7,5		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 200		
			min.	typ.	max.
Modulstreuintduktivität Stray inductance module		L _{sCE}		40	nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T _c = 25°C, pro Schalter / per switch	R _{CC'+EE'} R _{AA'+CC'}		4,00 3,00	mΩ
Lagertemperatur Storage temperature		T _{stg}	-40		125 °C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00		6,00 Nm
Gewicht Weight		G		300	g

prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0

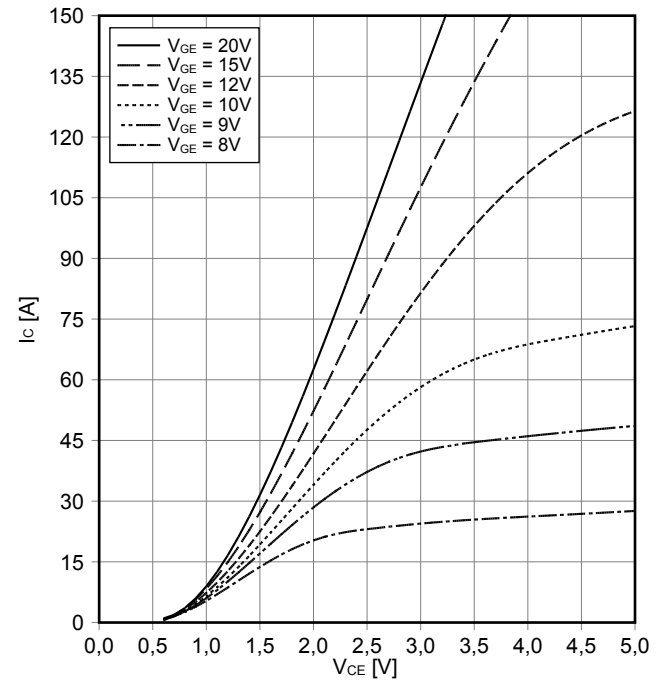
Ausgangskennlinie IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



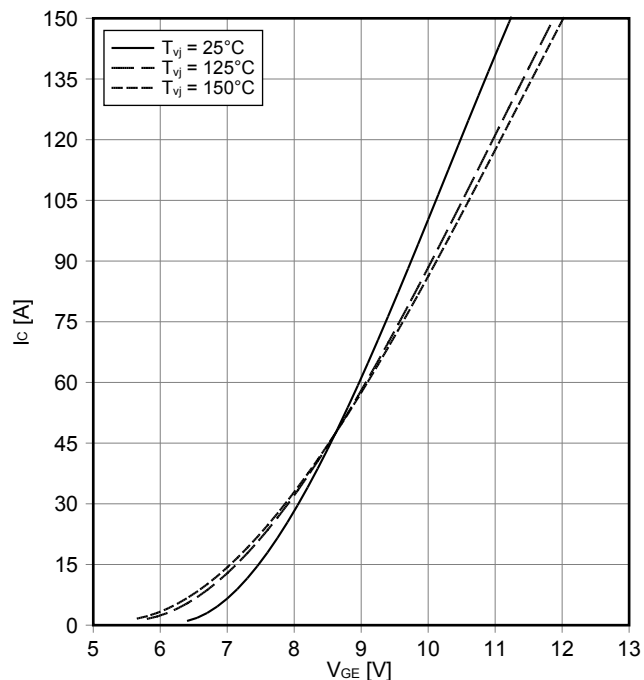
Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



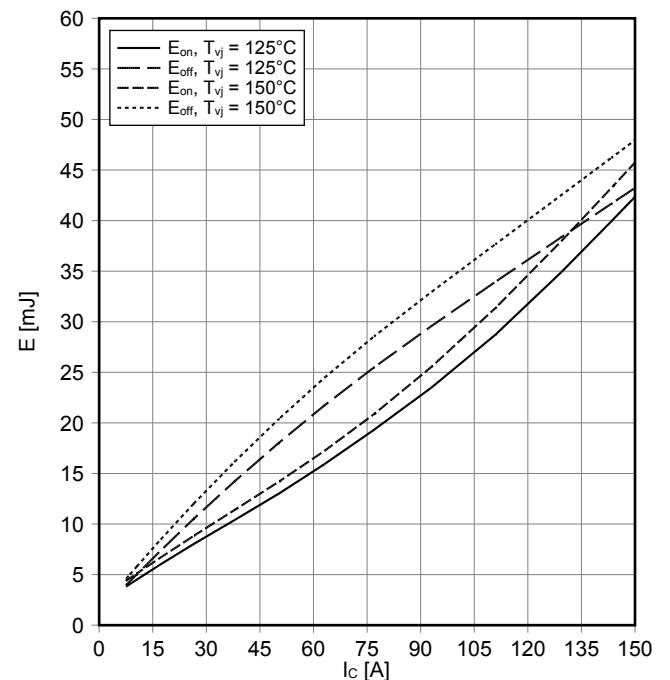
Übertragungscharakteristik IGBT, Wechselrichter (typisch)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 4.3\ \Omega$, $R_{Goff} = 4.3\ \Omega$, $V_{CE} = 900\text{ V}$

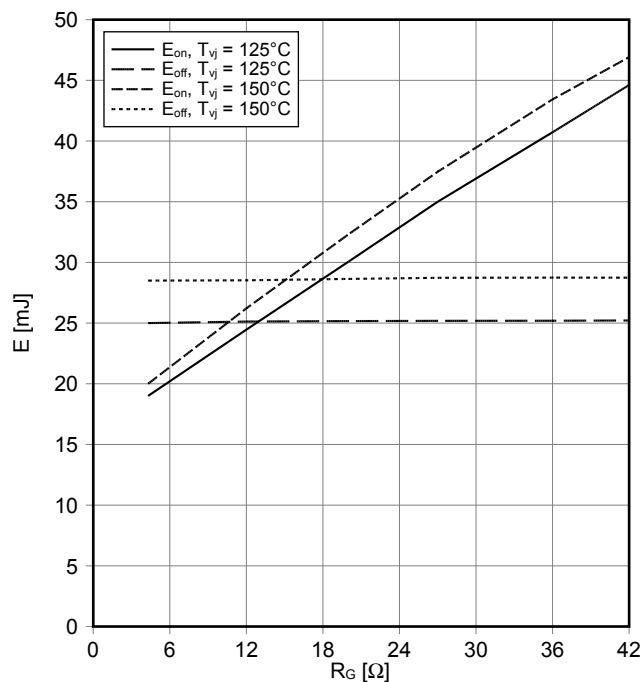


prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0



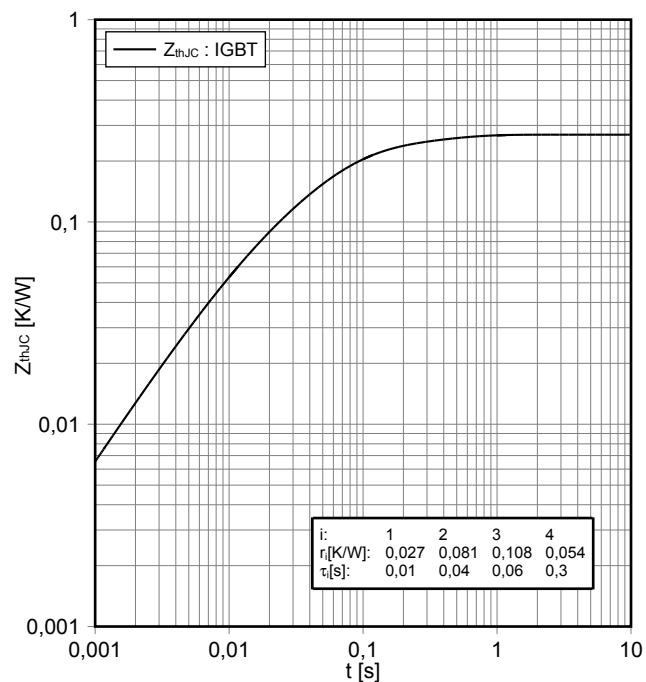
Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 75\text{ A}$, $V_{CE} = 900\text{ V}$



Transienter Wärmewiderstand IGBT, Wechselrichter
transient thermal impedance IGBT, Inverter

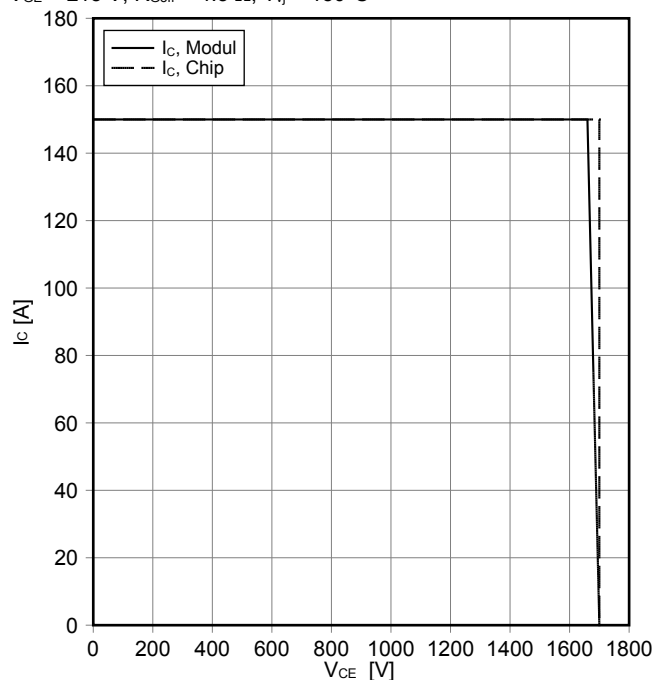
$Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

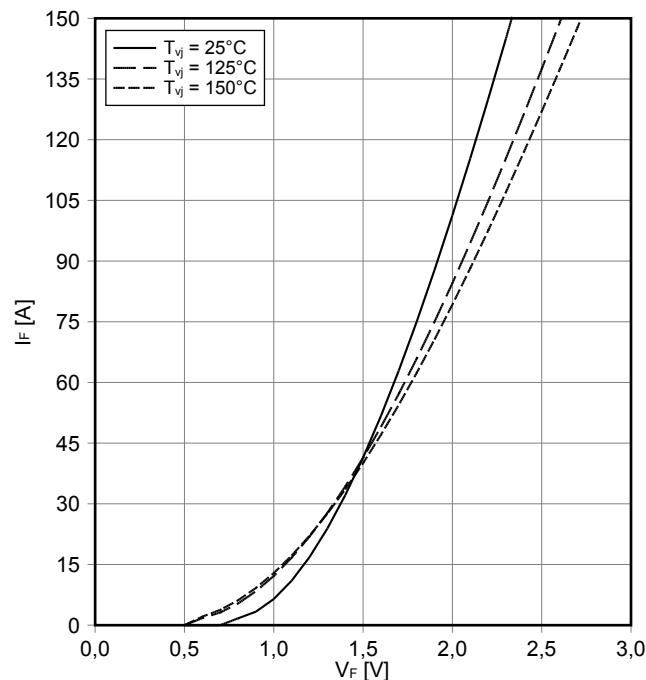
$I_C = f(V_{CE})$

$V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 4.3\ \Omega$, $T_{vj} = 150^\circ\text{C}$



Durchlasskennlinie der Diode, Wechselrichter (typisch)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$

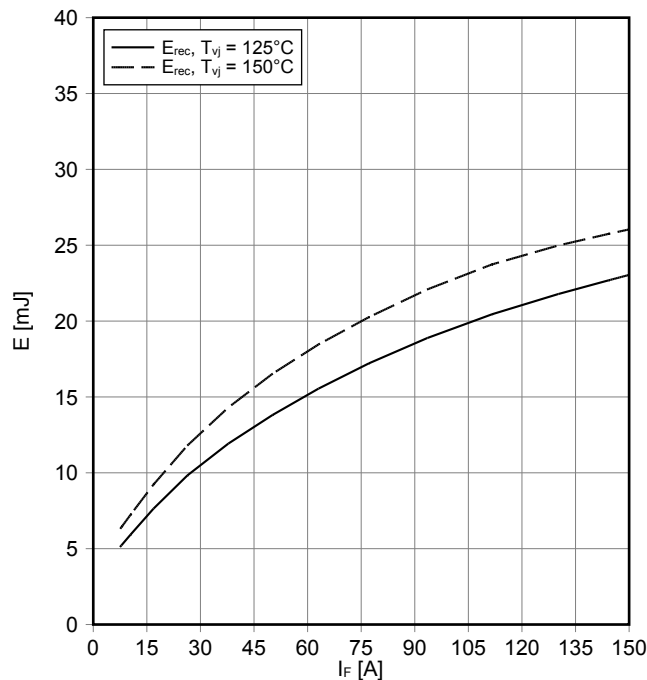


prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0



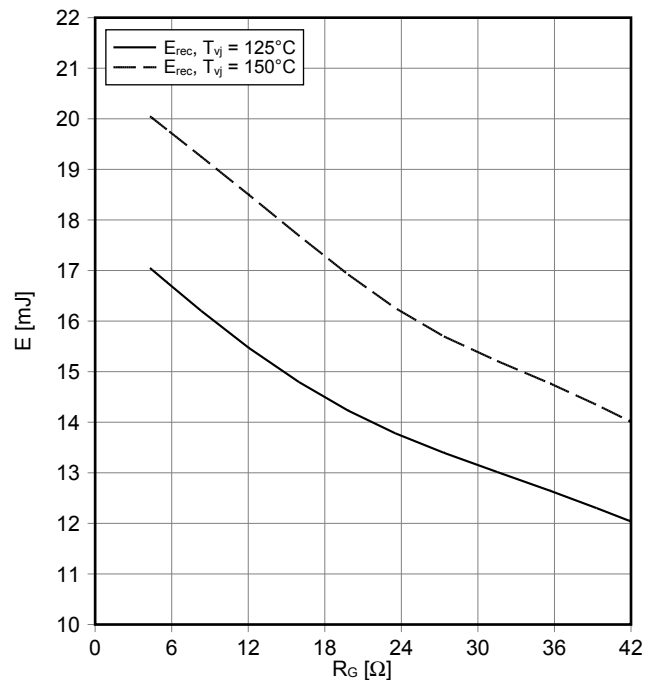
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 4.3 \Omega, V_{CE} = 900 V$



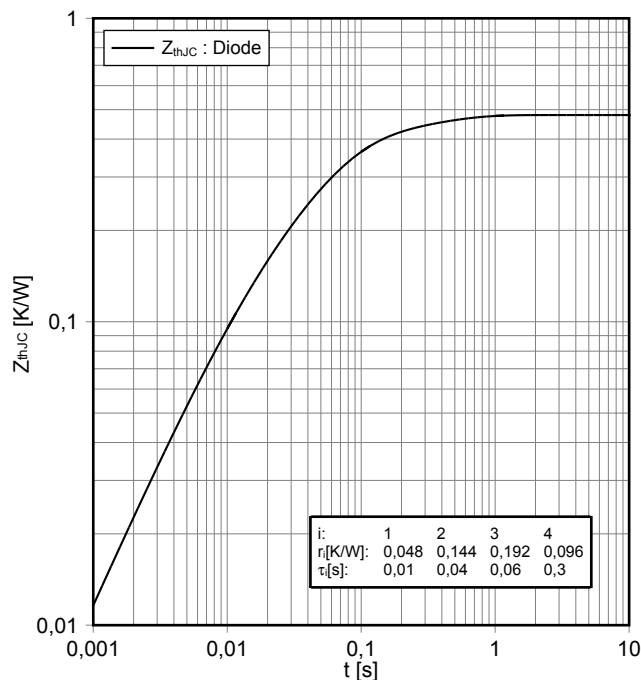
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 75 A, V_{CE} = 900 V$



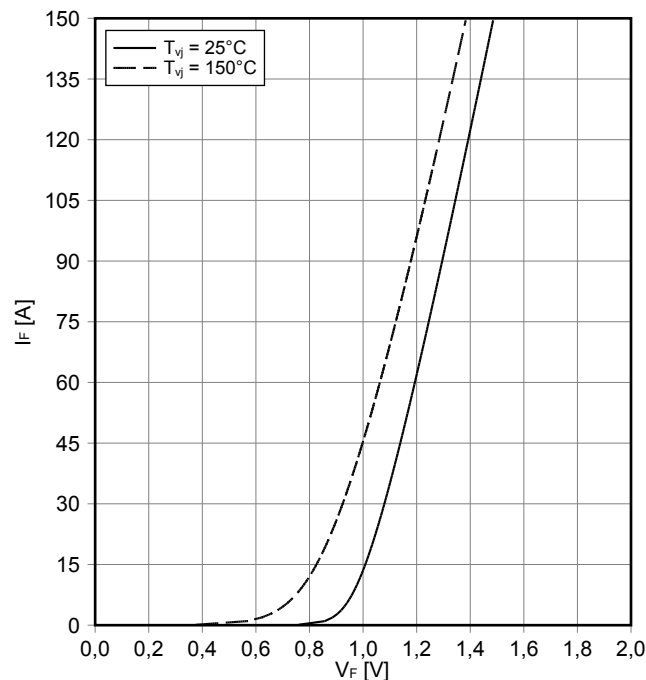
Transienter Wärmewiderstand Diode, Wechselrichter
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$



Durchlasskennlinie der Diode, Gleichrichter (typisch)
forward characteristic of Diode, Rectifier (typical)

$I_F = f(V_F)$

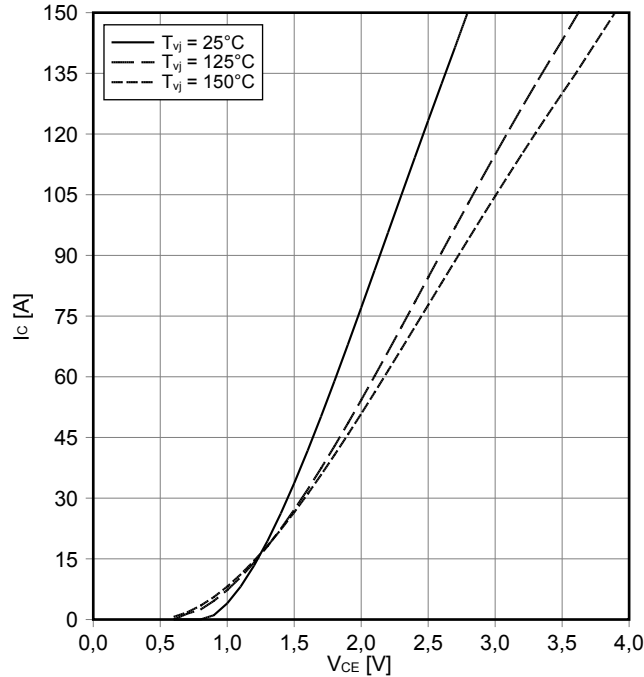


prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0



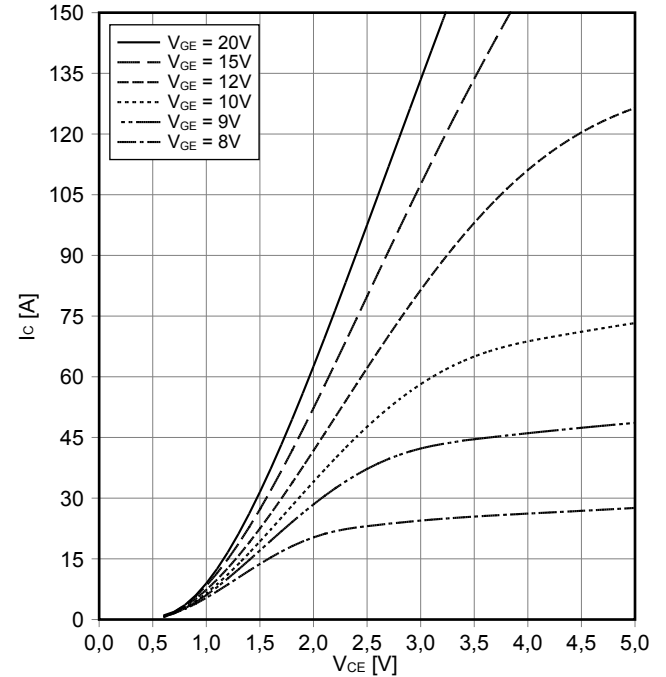
Ausgangskennlinie IGBT, Brems-Chopper (typisch)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



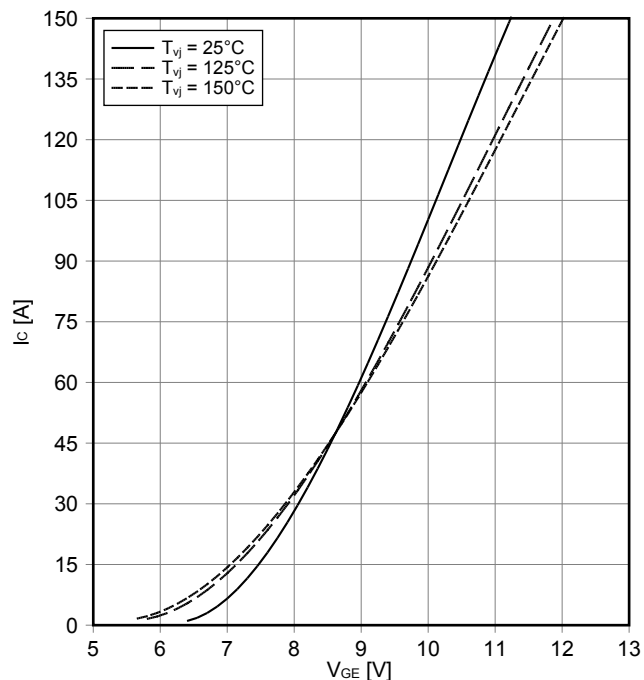
Ausgangskennlinienfeld IGBT, Brems-Chopper (typisch)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



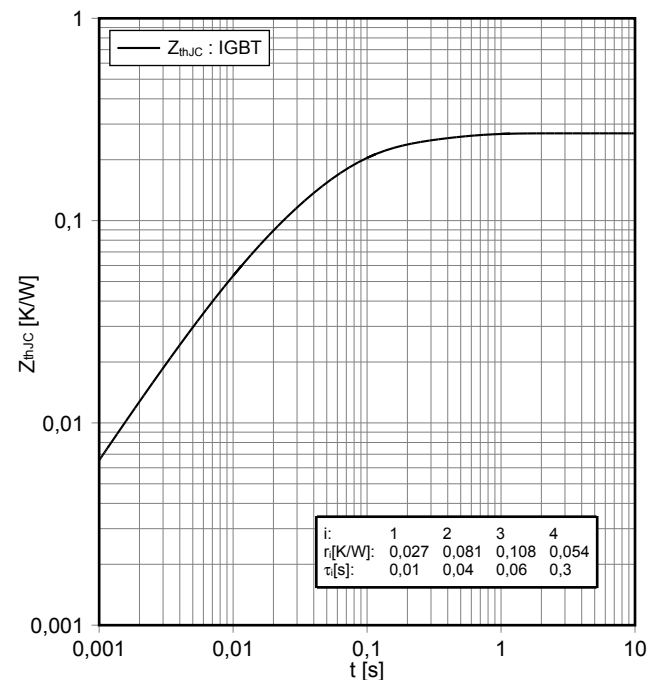
Übertragungscharakteristik IGBT, Brems-Chopper (typisch)
transfer characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Transienter Wärmewiderstand IGBT, Brems-Chopper
transient thermal impedance IGBT, Brake-Chopper

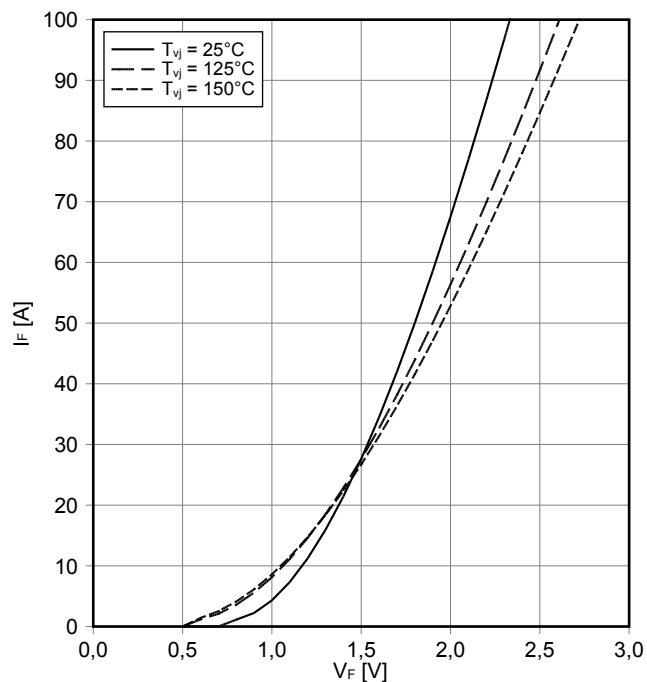
$Z_{thJC} = f(t)$



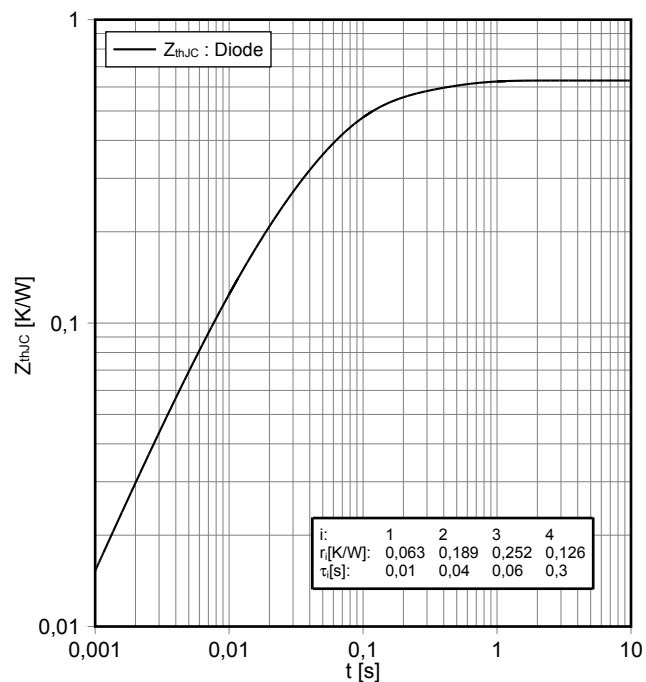
prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0



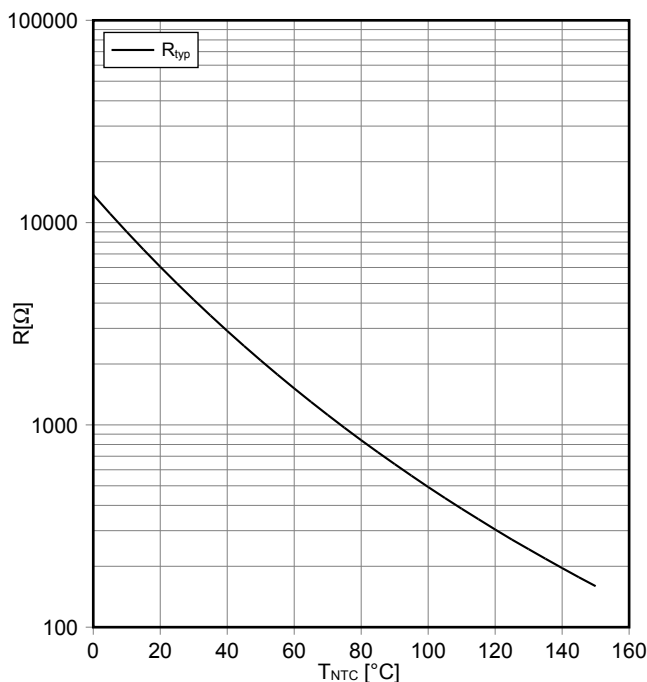
Durchlasskennlinie der Diode, Brems-Chopper (typisch)
forward characteristic of Diode, Brake-Chopper (typical)
 $I_F = f(V_F)$



Transienter Wärmewiderstand Diode, Brems-Chopper
transient thermal impedance Diode, Brake-Chopper
 $Z_{thJC} = f(t)$

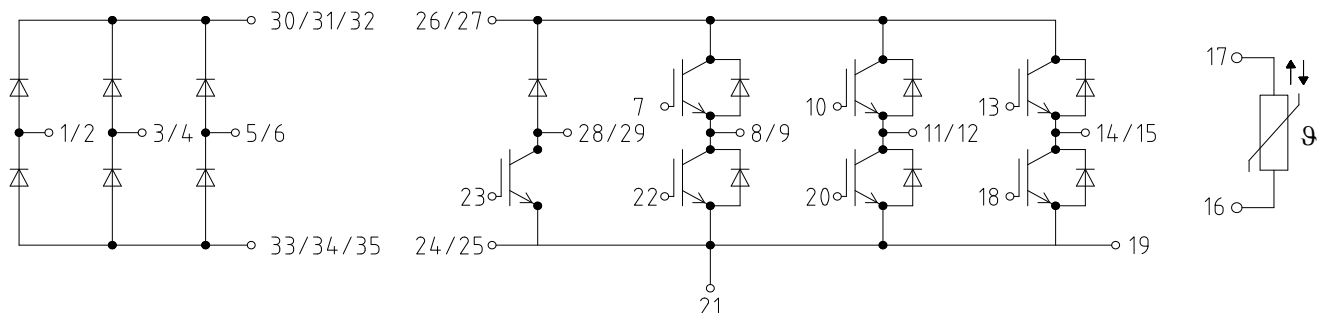


NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$

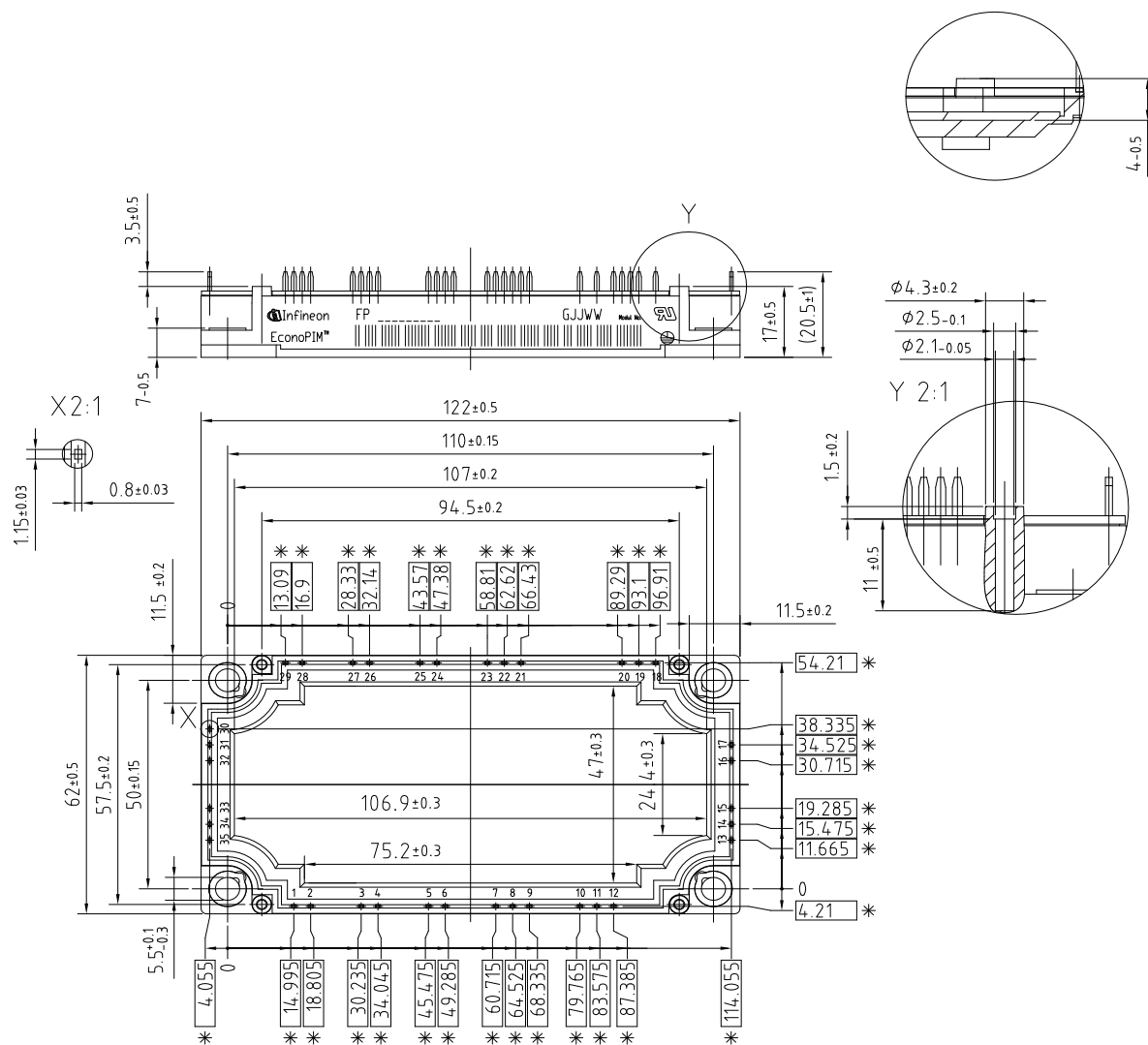


prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0

Schaltplan / Circuit diagram



Gehäuseabmessungen / Package outlines



* = alle Maße mit einer Toleranz von ± 0.5
 * = all dimensions with tolerance of ± 0.5

prepared by: MB	date of publication: 2016-06-07
approved by: RS	revision: V3.0